

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-17. (Canceled)

18. (Currently amended) A mold for producing a silicon ingot, comprising:

a bottom surface member; and

a plurality of lateral surface members combining with the bottom surface member,

and each lateral surface member comprising a first engaging structure on a first lateral end thereof and a second engaging structure on a second lateral end thereof, one of the first and second engaging structures of one of the plurality of lateral surface members engages with one of the first and second engaging structures of another one of the plurality of lateral surface members,

wherein the first and second engaging structures each comprises a projection and a recess, and ~~a shape of the first engaging structure and a shape of the second engaging structure are in an asymmetrical relationship with reference to a center line of the lateral surface member in a plan view thereof,~~

~~wherein the center line is between the first and second engaging structures and parallel with the first and second lateral ends~~

wherein the plurality of lateral surface members combined with a side surface of the bottom surface member and are upright so as to surround the bottom surface member, and

the mold for producing a silicon ingot further comprising:

a mold holder configured for placing the bottom surface member and the plurality of lateral surface members that are combined;

a wedge receiver is on an upper surface of the mold holder; and

a plurality of wedge members respectively positioned in clearances between the wedged receiver and outer peripheral surfaces of the plurality of lateral surface members.

19. (Canceled)

20. (Currently amended) The mold for producing a silicon ingot according to claim 18, wherein the number of the plurality of lateral surface members combining with the bottom surface member is four.

21. (Currently amended) The mold for producing a silicon ingot according to claim 18, wherein each of the engaging structures comprises one or more engaging surfaces that are substantially level with a bottom surface of the bottom surface member, and a distance between an upper side of the lateral surface member and the engaging surface closest to the upper side is in a range of not less than 1 cm nor more than 8 cm.

22. (Canceled)

23. (Currently amended) The mold for producing a silicon ingot according to claim 18, wherein the shapes of the engaging structures are in a point-symmetrical relationship with each other and with respect to a center point of the lateral surface member.

24-25. (Canceled)

26. (Currently amended) The mold for producing a silicon ingot according to claim [[25]] 18, wherein the wedge receiver is removable from the upper surface of the mold holder.

27. (Currently amended) The mold for producing a silicon ingot according to claim [[25]] 18, wherein

there exists a plurality of wedge receivers, and

a space between one of the plurality of wedge receivers and another one of the plurality of wedge receivers is adjustable, the another one wedge receiver is arranged at a position opposed to the one of the wedge receivers with the bottom surface member and the plurality of lateral surface members that are combined therebetween.

28. (Currently amended) The mold for producing a silicon ingot according to claim 18, further comprising a frame-shaped member which continuously surrounds an outer periphery of the plurality of lateral surface members integrated by engaging with each other and is configured for constraining displacement of the plurality of lateral surface members.

29. (Currently amended) The mold for producing a silicon ingot according to claim 18, further comprising:

a frame-shaped member continuously surrounding an outer periphery of the plurality of lateral surface members integrated by engaging with each other, with

~~play~~ a free space between the frame-shaped member and the plurality of lateral surface members; and

a plurality of pressing jigs respectively arranged in clearances between the frame-shaped member and outer corners formed by the lateral surface members adjacent to each other, and configured for constraining displacement of the plurality of lateral surface members.

30. (Currently amended) The mold for producing a silicon ingot according to claim 29, wherein one of the plurality of pressing jigs has two jig surfaces respectively contacting with outer peripheral surfaces of two of the plurality of lateral surface members, the outer peripheral surfaces form the outer corner of the mold for producing a silicon ingot.

31. (Currently amended) The mold for producing a silicon ingot according to claim 30, wherein the one of the plurality of pressing jigs has a relief groove located corresponding to the outer corner of the mold for producing a silicon ingot so as not to directly contact with each other.

32. (Currently amended) The mold for producing a silicon ingot according to claim 29, wherein the frame-shaped member has a projection in an inner periphery thereof, the projection contacts with the lateral surface member facing therewith for constraining displacement of the plurality of lateral surface members.

33. (Currently amended) The mold for producing a silicon ingot according to claim 28, wherein each of the engaging structures comprises one or more engaging surfaces that are substantially level with the bottom surface of the bottom surface

member, and the frame-shaped members are respectively arranged at positions of the engaging surfaces.

34. (Currently amended) The mold for producing a silicon ingot according to claim 18, further comprising a mold release material applied to

a mold inner surface comprising a surface of the bottom surface member and surfaces of the plurality of lateral surface members and

locking sections formed by the bottom surface member and the plurality of lateral surface members.

35. (Canceled)

36. (Currently amended) A polycrystalline silicon substrate producing method, comprising:

a step of producing a silicon ingot by using the mold for producing a silicon ingot according to any one of claims ~~18 to 34~~ 18, 20, 21, 23, and 26-34; and

a step of obtaining a polycrystalline silicon substrate from the silicon ingot.

37. (Currently amended) The mold for producing a silicon ingot according to claim 18, wherein the projection and the recess are aligned along the lateral end of the lateral surface member.

38. (Currently amended) The mold for producing a silicon ingot according to claim 18, wherein the projection and the recess of each of the first and second engaging structures are arranged in a lengthwise direction of the lateral surface member.